

1N5817WS - 1N5819WS

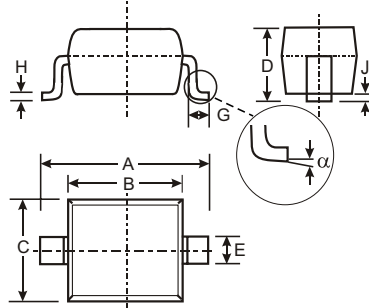
SURFACE MOUNT SCHOTTKY BARRIER DIODE

Features

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOD-323
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Leads: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Polarity: Cathode Band
- Type Codes: 1N5819WS S4
1N5818WS S5 or S4
1N5817WS S6 or S5 or S4
- Weight: 0.004 grams (approximate)



SOD-323		
Dim	Min	Max
A	2.30	2.70
B	1.60	1.80
C	1.20	1.40
D	1.05 Typical	
E	0.25	0.35
G	0.20	0.40
H	0.10	0.15
J	0.05 Typical	
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	1N5819WS	1N5818WS	1N5817WS	Unit
Peak Repetitive Reverse Voltage	V_{RRM}				
Working Peak Reverse Voltage	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current (Note 1)	I_{FM}	350			mA
Non-Repetitive Peak Forward Surge Current @ $t \leq 1.0\text{s}$	I_{FSM}	1.5			A
Power Dissipation (Note 1)	P_d	200			mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625			$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_i, T_{STG}	-65 to +125			$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Reverse Breakdown Voltage (Note 2)	$V_{(BR)R}$	40 30 20	—	—	V	$I_R = 100\mu\text{A}$ $I_R = 100\mu\text{A}$ $I_R = 100\mu\text{A}$
Forward Voltage Drop	V_F	—	—	0.37 0.60	V	$I_F = 20\text{mA}$ $I_F = 200\text{mA}$
Peak Reverse Current (Note 2)	I_R	—	—	5.0	μA	$V_R = 30\text{V}$ $V_R = 20\text{V}$ $V_R = 10\text{V}$
Total Capacitance	C_T	—	28	—	pF	$V_R = 0\text{V}, f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	—	10	—	ns	$I_F = I_R = 200\text{mA}$, $I_{Tr} = 0.1 \times I_R, R_L = 100\Omega$

- Note: 1. Short duration test pulse used to minimize self-heating effect.
2. No purposefully added lead.

